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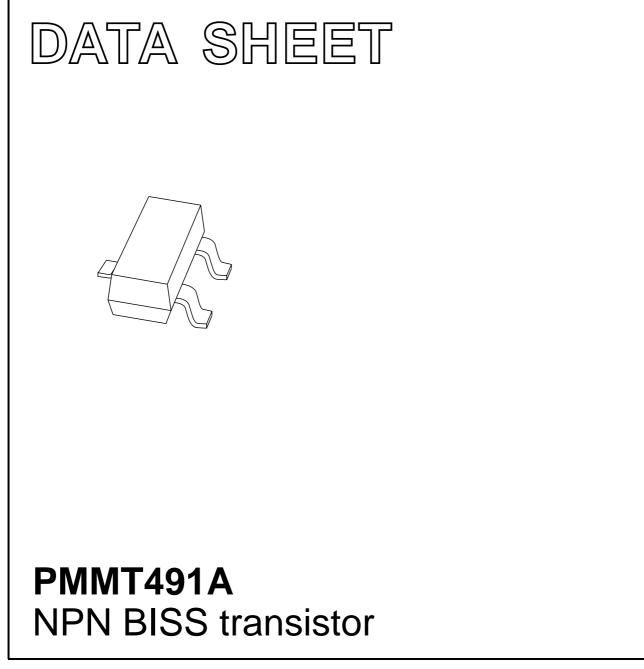
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2001 Jun 11 2004 Jan 13



Product data sheet

NPN BISS transistor

FEATURES

- High current (max. 1 A)
- Low collector-emitter saturation voltage ensures reduced power consumption.

APPLICATIONS

• Battery powered units where high current and low power consumption are important.

DESCRIPTION

NPN BISS (Breakthrough In Small Signal) transistor in a SOT23 plastic package. PNP complement: PMMT591A.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾	
PMMT491A	9A*	

Note

- 1. * = p : Made in Hong Kong.
- * = t : Made in Malaysia.

* = W : Made in China.

ORDERING INFORMATION

ТҮРЕ	PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION
PMMT491A	_	plastic surface mounted package; 3 leads	SOT23

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	40	V
V _{CEO}	collector-emitter voltage	open base	-	40	V
V _{EBO}	emitter-base voltage	open collector	-	5	V
I _C	collector current (DC)		-	1	А
I _{CM}	peak collector current		-	2	А
I _{BM}	peak base current		-	1	А
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C; note 1$	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

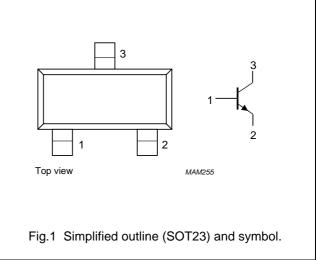
Note

1. Transistor mounted on an FR4 printed-circuit board.

PMMT491A

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



PMMT491A

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

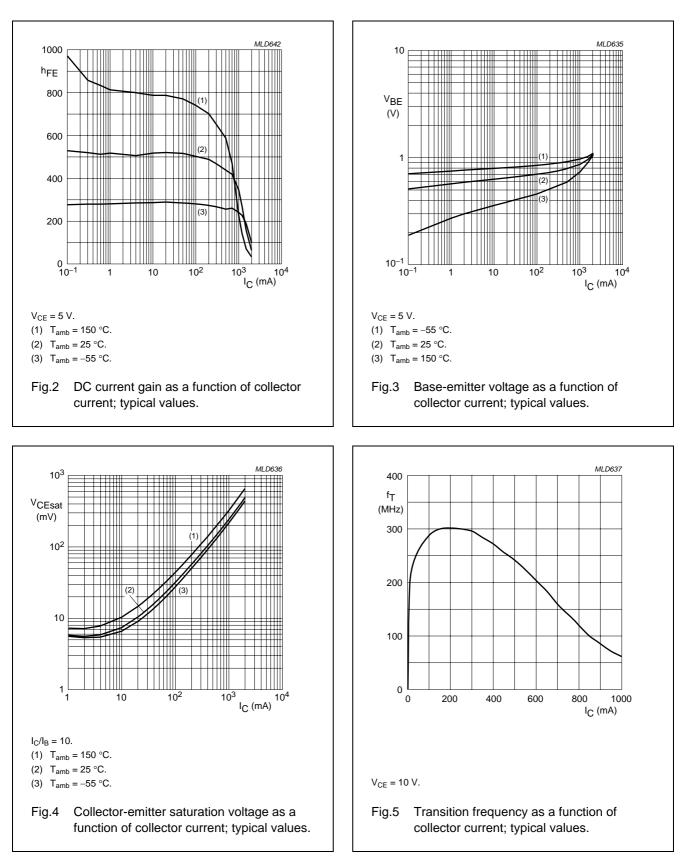
 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current	I _E = 0; V _{CB} = 30 V	-	100	nA
I _{CEO}	collector cut-off current	I _B = 0; V _{CE} = 30 V	-	100	nA
I _{EBO}	emitter cut-off current	I _C = 0; V _{EB} = 5 V	-	100	nA
h _{FE}	DC current gain	V _{CE} = 5 V; note 1			
		I _C = 1 mA	300	-	
		I _C = 500 mA	300	900	
		I _C = 1 A	200	-	
V _{CEsat}	collector-emitter saturation voltage	note 1			
		I _C = 100 mA; I _B = 1 mA	-	200	mV
		I _C = 500 mA; I _B = 50 mA	-	300	mV
		I _C = 1 A; I _B = 100 mA	_	500	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA; note 1	-	1.2	V
V _{BE}	base-emitter voltage	V _{CE} = 5 V; I _C = 1 A; note 1	_	1.1	V
C _c	collector capacitance	I _E = I _e = 0; V _{CB} = 10 V; f = 1 MHz	_	10	pF
f _T	transition frequency	I _C = 50 mA; V _{CE} = 10 V; f = 100 MHz	150	-	MHz

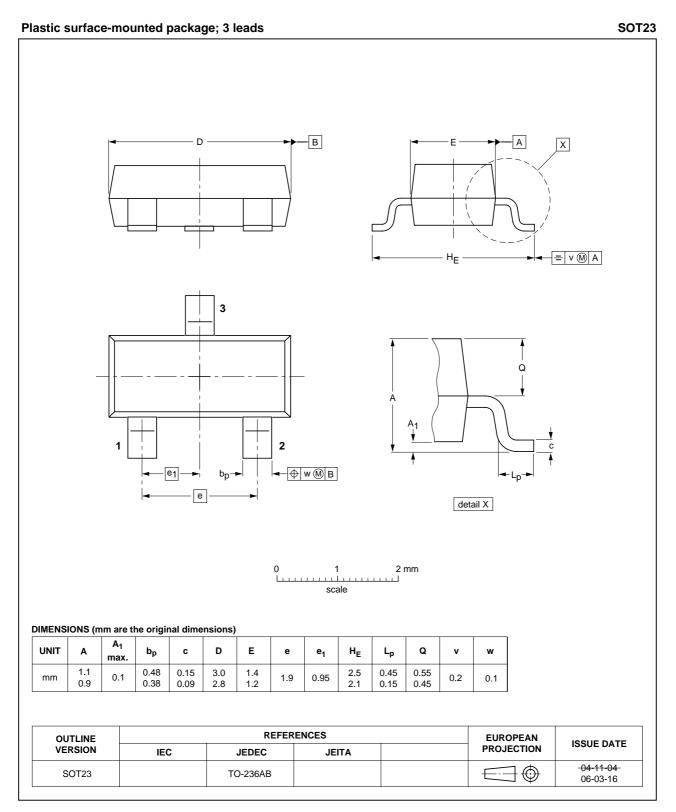
Note

1. Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02.$

PMMT491A



PACKAGE OUTLINE



PMMT491A

PMMT491A

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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